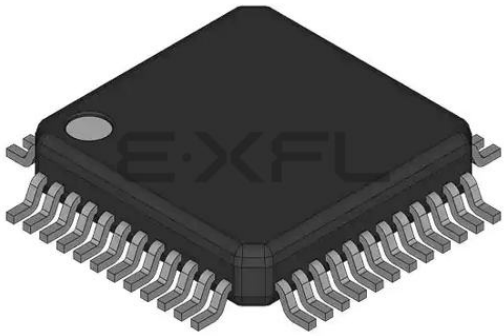

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	40MHz
Connectivity	CSIO, EBI/EMI, I²C, LINbus, UART/USART, USB
Peripherals	LVD, POR, WDT
Number of I/O	36
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 8x12b; D/A 1x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/rochester-electronics/mb9af421kpmc-g-jne2

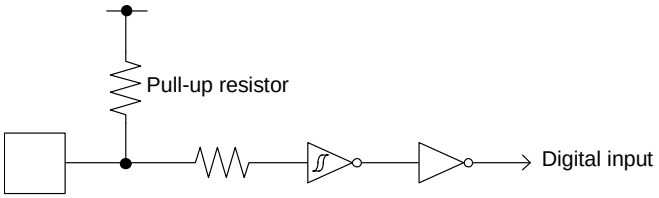
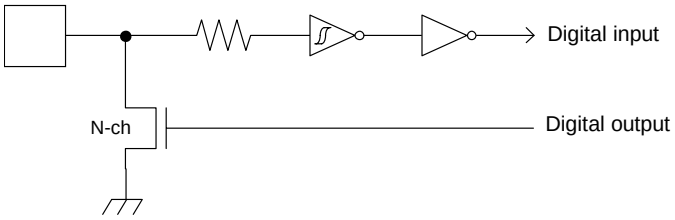
2. Packages

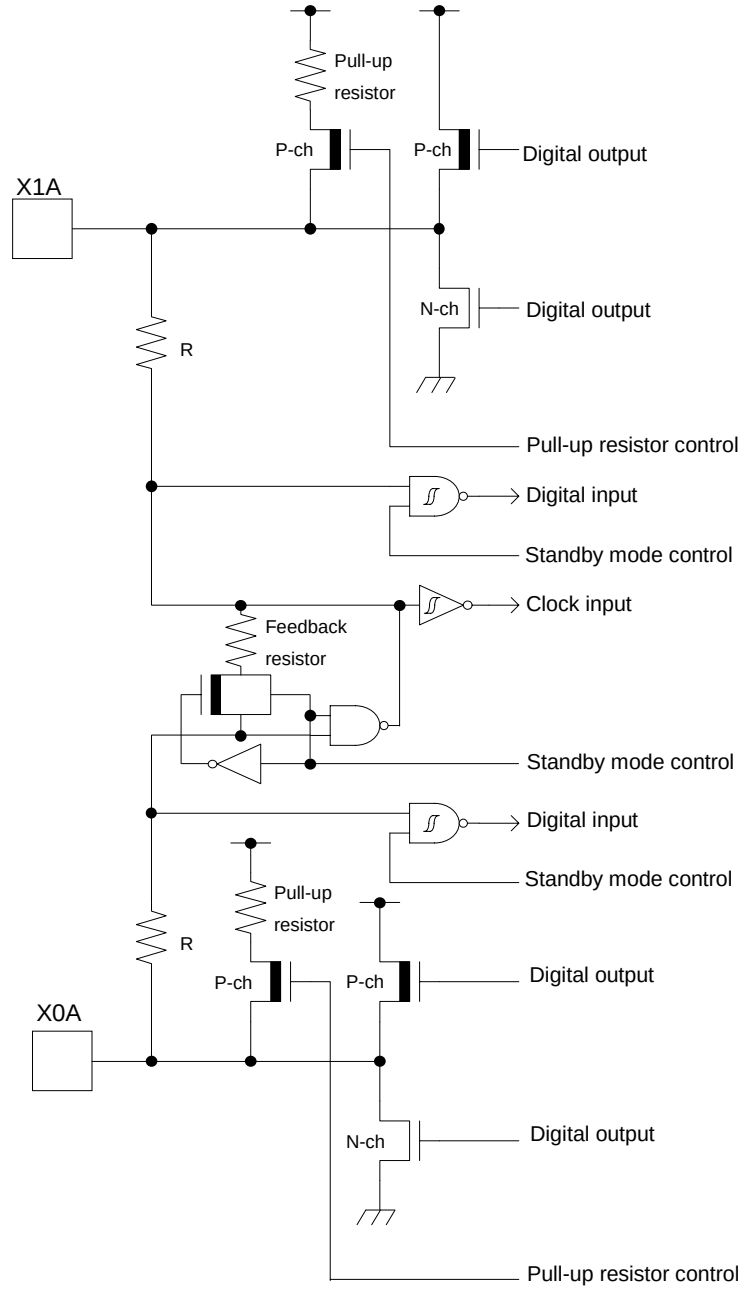
Package \ Product name	MB9AF421K	MB9AF421L
LQFP: LQA048 (0.5 mm pitch)	❍	-
QFN: WNY048 (0.5 mm pitch)	❍	-
LQFP: LQC052 (0.65 mm pitch)	❍	-
LQFP: LQD064 (0.5 mm pitch)	-	❍
LQFP: LQG064 (0.65 mm pitch)	-	❍
QFN: WNS064 (0.5 mm pitch)	-	❍

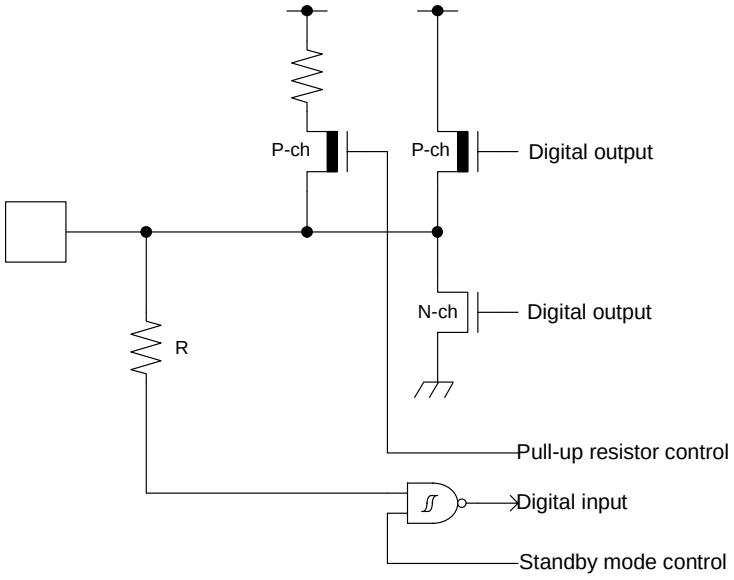
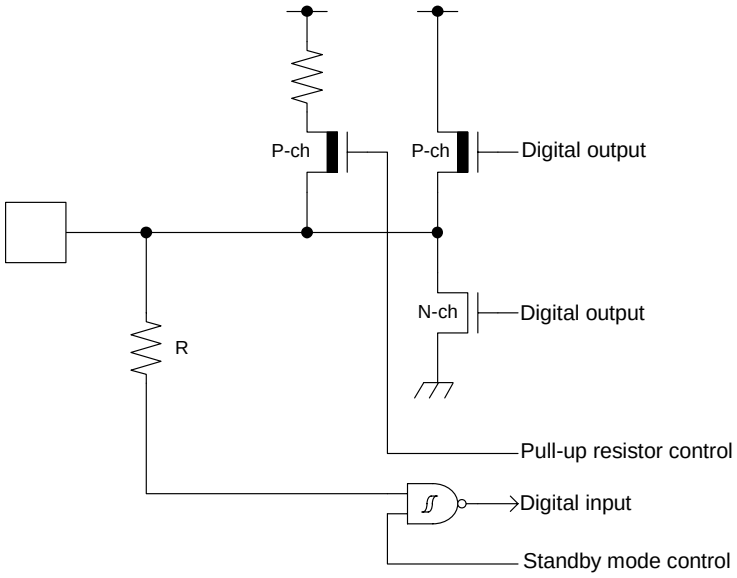
❍: Supported

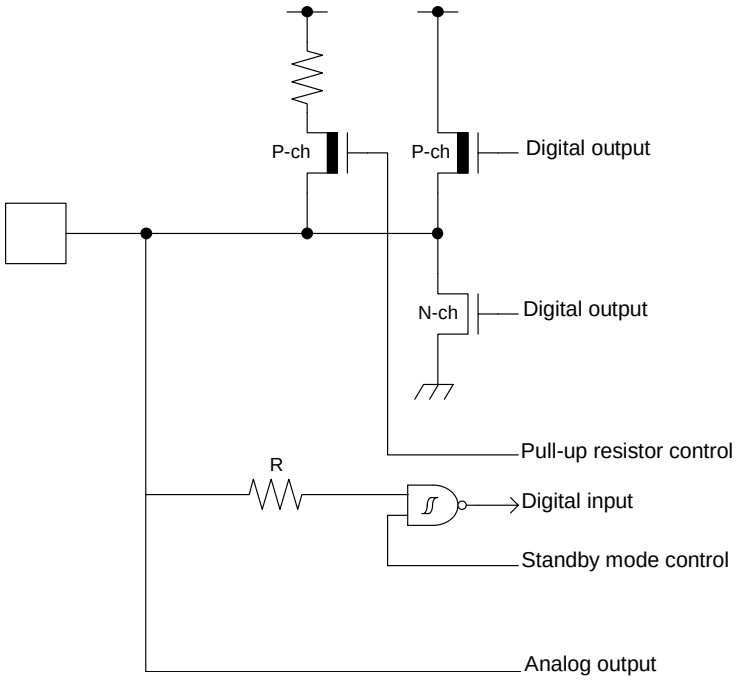
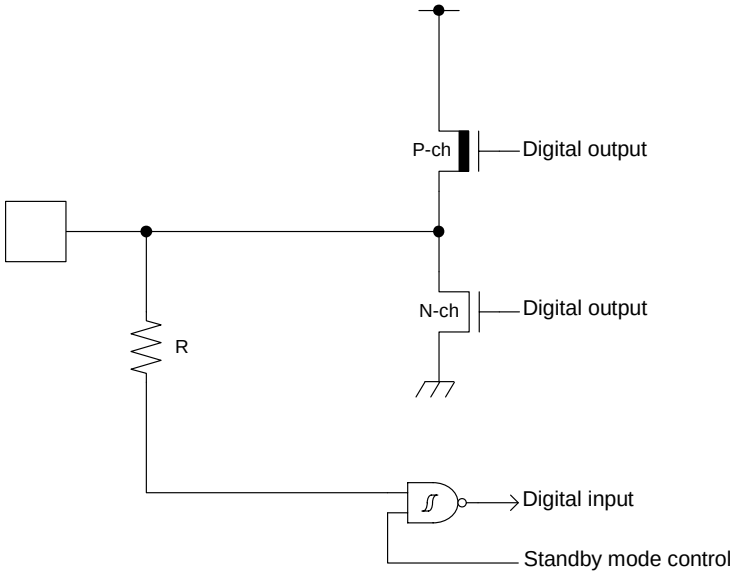
Note:

- *See Package Dimensions for detailed information on each package.*

Type	Circuit	Remarks
B		• CMOS level hysteresis input • Pull-up resistor : Approximately 50 kΩ
C		• Open drain output • CMOS level hysteresis input

Type	Circuit	Remarks
D		It is possible to select the sub oscillation / GPIO function When the sub oscillation is selected. • Oscillation feedback resistor : Approximately 5 MΩ • With Standby mode control When the GPIO is selected. • CMOS level output. • CMOS level hysteresis input • With pull-up resistor control • With standby mode control • Pull-up resistor : Approximately 50 kΩ • I_{OH}= -4 mA, I_{OL}= 4 mA

Type	Circuit	Remarks
G		• CMOS level output • CMOS level hysteresis input • With pull-up resistor control • With standby mode control • Pull-up resistor : Approximately 50 kΩ • I_{OH}= -12 mA, I_{OL}= 12 mA • +B input is available
H		• CMOS level output • CMOS level hysteresis input • 5 V tolerant • With pull-up resistor control • With standby mode control • Pull-up resistor : Approximately 50 kΩ • I_{OH}= -4 mA, I_{OL}= 4 mA • Available to control PZR registers. Only P51, P52. • When this pin is used as an I^2C pin, the digital output P-ch transistor is always off

Type	Circuit	Remarks
K		• CMOS level output • CMOS level hysteresis input • With input control • Analog output • With pull-up resistor control • With standby mode control • Pull-up resistor : Approximately 50 kΩ • I_{OH} = -4 mA, I_{OL} = 4 mA • When this pin is used as an I^2C pin, the digital output P-ch transistor is always off
L		• CMOS level output • CMOS level hysteresis input • With standby mode control • I_{OH}= -4 mA, I_{OL}= 4 mA

Precautions Related to Usage of Devices

Cypress semiconductor devices are intended for use in standard applications (computers, office automation and other office equipment, industrial, communications, and measurement equipment, personal or household devices, etc.).

CAUTION: Customers considering the use of our products in special applications where failure or abnormal operation may directly affect human lives or cause physical injury or property damage, or where extremely high levels of reliability are demanded (such as aerospace systems, atomic energy controls, sea floor repeaters, vehicle operating controls, medical devices for life support, etc.) are requested to consult with sales representatives before such use. The company will not be responsible for damages arising from such use without prior approval.

6.2 Precautions for Package Mounting

Package mounting may be either lead insertion type or surface mount type. In either case, for heat resistance during soldering, you should only mount under Cypress' recommended conditions. For detailed information about mount conditions, contact your sales representative.

Lead Insertion Type

Mounting of lead insertion type packages onto printed circuit boards may be done by two methods: direct soldering on the board, or mounting by using a socket.

Direct mounting onto boards normally involves processes for inserting leads into through-holes on the board and using the flow soldering (wave soldering) method of applying liquid solder. In this case, the soldering process usually causes leads to be subjected to thermal stress in excess of the absolute ratings for storage temperature. Mounting processes should conform to Cypress recommended mounting conditions.

If socket mounting is used, differences in surface treatment of the socket contacts and IC lead surfaces can lead to contact deterioration after long periods. For this reason it is recommended that the surface treatment of socket contacts and IC leads be verified before mounting.

Surface Mount Type

Surface mount packaging has longer and thinner leads than lead-insertion packaging, and therefore leads are more easily deformed or bent. The use of packages with higher pin counts and narrower pin pitch results in increased susceptibility to open connections caused by deformed pins, or shorting due to solder bridges.

You must use appropriate mounting techniques. Cypress recommends the solder reflow method, and has established a ranking of mounting conditions for each product. Users are advised to mount packages in accordance with Cypress ranking of recommended conditions.

Lead-Free Packaging

CAUTION: When ball grid array (BGA) packages with Sn-Ag-Cu balls are mounted using Sn-Pb eutectic soldering, junction strength may be reduced under some conditions of use.

Storage of Semiconductor Devices

Because plastic chip packages are formed from plastic resins, exposure to natural environmental conditions will cause absorption of moisture. During mounting, the application of heat to a package that has absorbed moisture can cause surfaces to peel, reducing moisture resistance and causing packages to crack. To prevent, do the following:

1. Avoid exposure to rapid temperature changes, which cause moisture to condense inside the product. Store products in locations where temperature changes are slight.
2. Use dry boxes for product storage. Products should be stored below 70% relative humidity, and at temperatures between 5°C and 30°C.
   When you open Dry Package that recommends humidity 40% to 70% relative humidity.
3. When necessary, Cypress packages semiconductor devices in highly moisture-resistant aluminum laminate bags, with a silica gel desiccant. Devices should be sealed in their aluminum laminate bags for storage.
4. Avoid storing packages where they are exposed to corrosive gases or high levels of dust.

Baking

Packages that have absorbed moisture may be de-moisturized by baking (heat drying). Follow the Cypress recommended conditions for baking.

Condition: 125°C/24 h

Static Electricity

Because semiconductor devices are particularly susceptible to damage by static electricity, you must take the following precautions:

1. Maintain relative humidity in the working environment between 40% and 70%. Use of an apparatus for ion generation may be needed to remove electricity.
2. Electrically ground all conveyors, solder vessels, soldering irons and peripheral equipment.
3. Eliminate static body electricity by the use of rings or bracelets connected to ground through high resistance (on the level of 1 MΩ).
   Wearing of conductive clothing and shoes, use of conductive floor mats and other measures to minimize shock loads is recommended.
4. Ground all fixtures and instruments, or protect with anti-static measures.
5. Avoid the use of styrofoam or other highly static-prone materials for storage of completed board assemblies.

6.3 Precautions for Use Environment

Reliability of semiconductor devices depends on ambient temperature and other conditions as described above.

For reliable performance, do the following:

1. Humidity

   Prolonged use in high humidity can lead to leakage in devices as well as printed circuit boards. If high humidity levels are anticipated, consider anti-humidity processing.
2. Discharge of Static Electricity

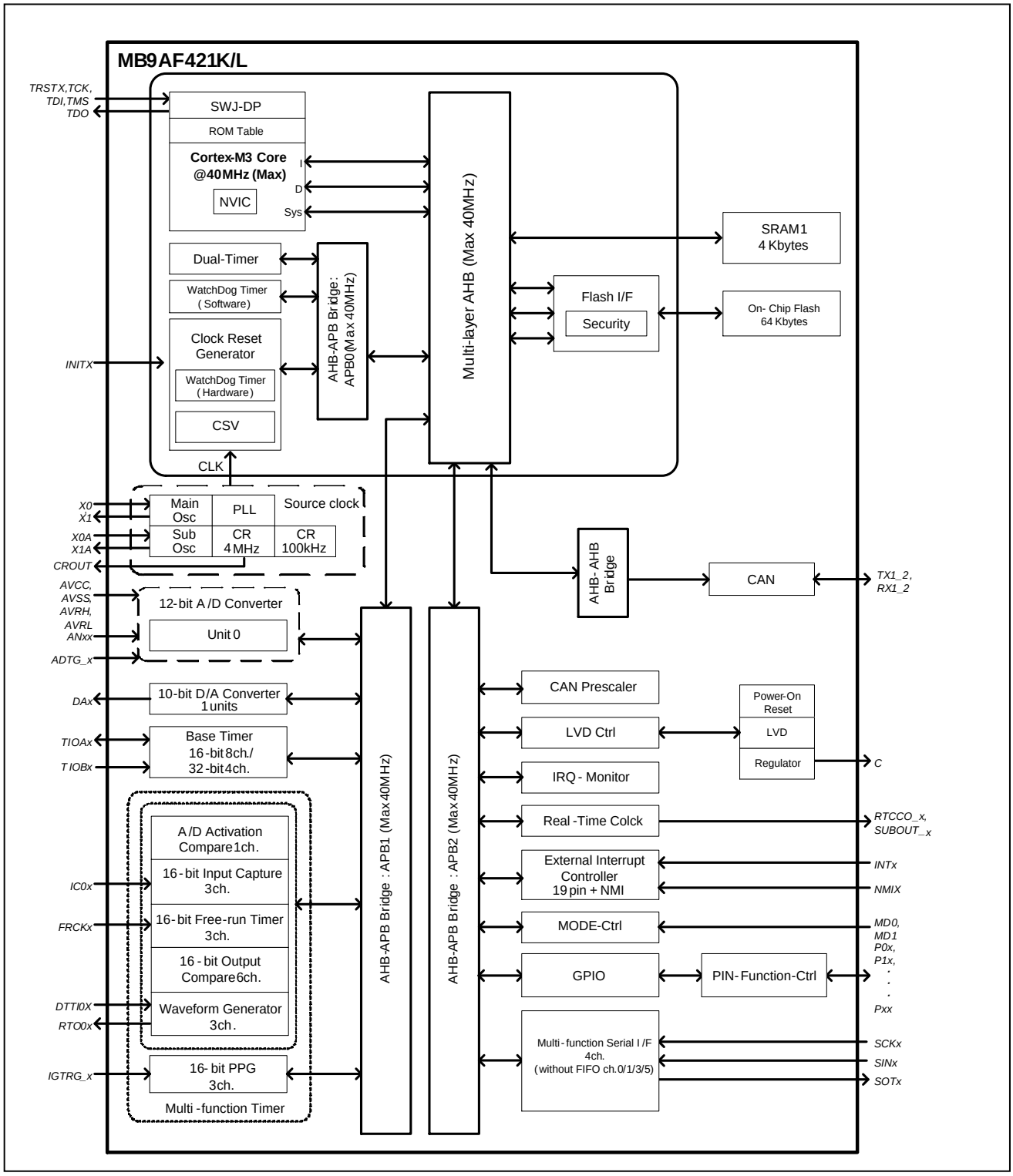
   When high-voltage charges exist close to semiconductor devices, discharges can cause abnormal operation. In such cases, use anti-static measures or processing to prevent discharges.
3. Corrosive Gases, Dust, or Oil

   Exposure to corrosive gases or contact with dust or oil may lead to chemical reactions that will adversely affect the device. If you use devices in such conditions, consider ways to prevent such exposure or to protect the devices.
4. Radiation, Including Cosmic Radiation

   Most devices are not designed for environments involving exposure to radiation or cosmic radiation. Users should provide shielding as appropriate.
5. Smoke, Flame
   CAUTION: Plastic molded devices are flammable, and therefore should not be used near combustible substances.
   If devices begin to smoke or burn, there is danger of the release of toxic gases.

Customers considering the use of Cypress products in other special environmental conditions should consult with sales representatives.

8. Block Diagram

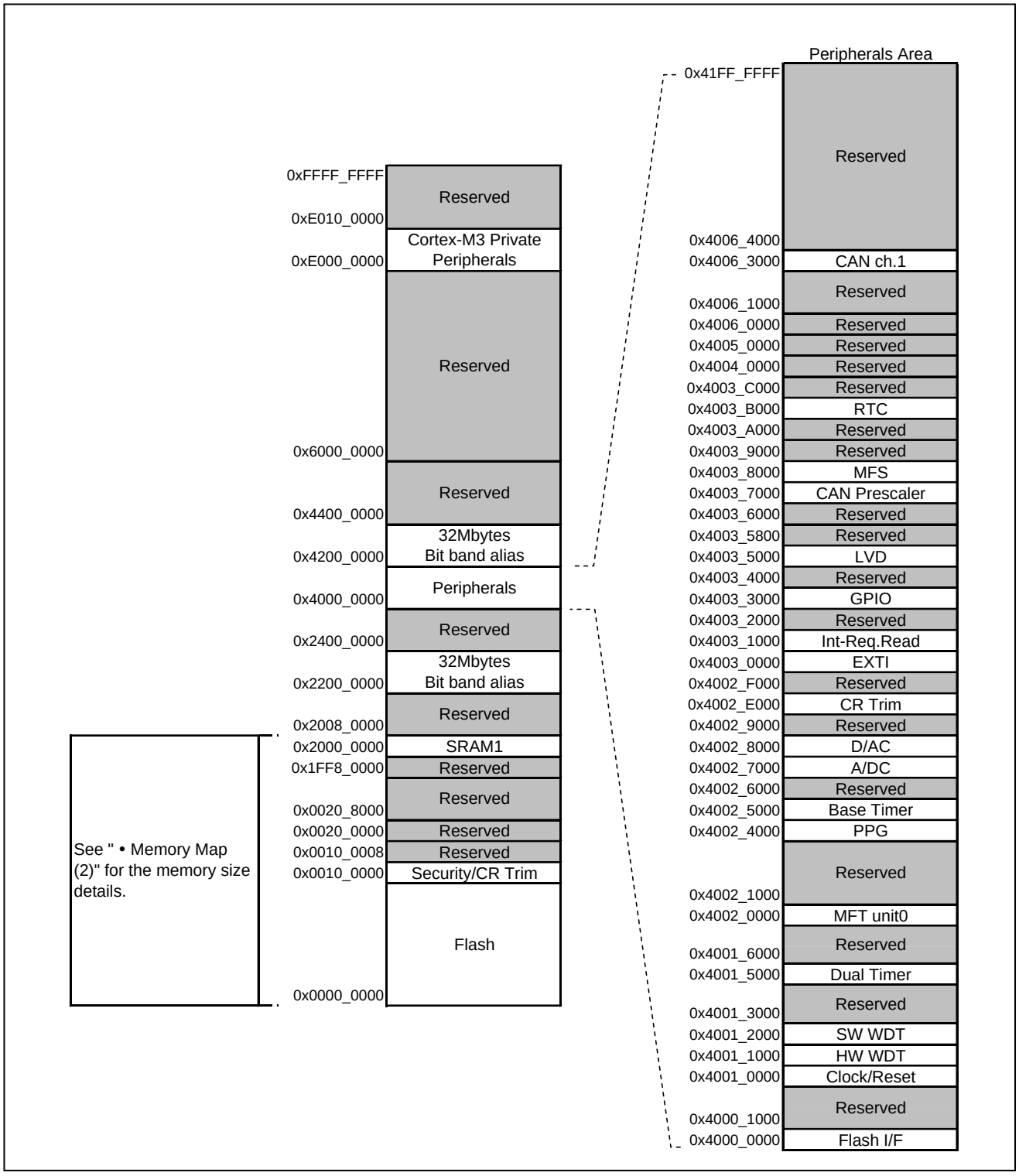


9. Memory Size

See Memory size in Product Lineup to confirm the memory size.

10. Memory Map

Memory Map (1)



11. Pin Status in Each CPU State

The terms used for pin status have the following meanings.

- INITX=0

  This is the period when the INITX pin is the L level.

- INITX=1

  This is the period when the INITX pin is the H level.

- SPL=0

  This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 0.

- SPL=1

  This is the status that the standby pin level setting bit (SPL) in the standby mode control register (STB_CTL) is set to 1.

- Input enabled

  Indicates that the input function can be used.

- Internal input fixed at 0

  This is the status that the input function cannot be used. Internal input is fixed at L.

- Hi-Z

  Indicates that the pin drive transistor is disabled and the pin is put in the Hi-Z state.

- Setting disabled

  Indicates that the setting is disabled.

- Maintain previous state

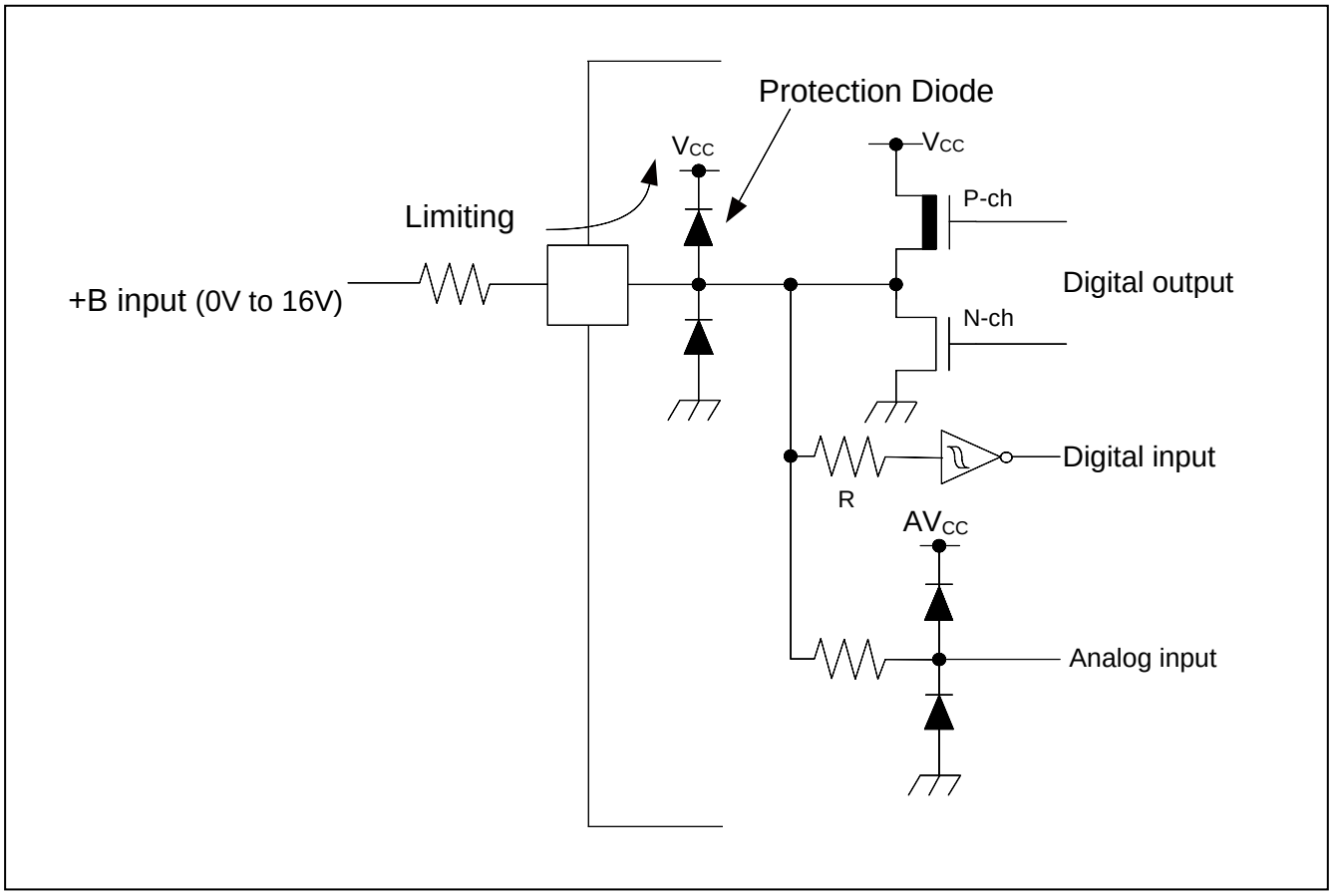
  Maintains the state that was immediately prior to entering the current mode.
  If a built-in peripheral function is operating, the output follows the peripheral function.
  If the pin is being used as a port, that output is maintained.

- Analog input is enabled

  Indicates that the analog input is enabled.

*7:

- See List of Pin Functions and I/O Circuit Type about +B input available pin.
- Use within recommended operating conditions.
- Use at DC voltage (current) the +B input.
- The +B signal should always be applied a limiting resistance placed between the +B signal and the device.
- The value of the limiting resistance should be set so that when the +B signal is applied the input current to the device pin does not exceed rated values, either instantaneously or for prolonged periods.
- Note that when the device drive current is low, such as in the low-power consumption modes, the +B input potential may pass through the protective diode and increase the potential at the VCC and AVCC pin, and this may affect other devices.
- Note that if a +B signal is input when the device power supply is off (not fixed at 0 V), the power supply is provided from the pins, so that incomplete operation may result.
- The following is a recommended circuit example (I/O equivalent circuit).



WARNING:

- *Semiconductor devices may be permanently damaged by application of stress (including, without limitation, voltage, current or temperature) in excess of absolute maximum ratings.*
  Do not exceed any of these ratings.

12.3 DC Characteristics

12.3.1 Current Rating

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = AVRL = 0V, T_A = - 40°C to + 105°C)

Parameter	Symbol	Pin name	Conditions		Value		Unit	Remarks
					Typ	Max		
Run mode current	I_{CC}	VCC	PLL Run mode	CPU: 40 MHz, Peripheral: 40 MHz Instruction on Flash	15.5	16	mA	*1, *5
				CPU: 40 MHz, Peripheral: the clock stops NOP operation Instruction on Flash	9	10.6	mA	*1, *5
				CPU: 40 MHz, Peripheral: 40 MHz Instruction on RAM	14	15	mA	*1
			High-speed CR Run mode	CPU/ Peripheral: 4 MHz*2 Instruction on Flash	1.7	3.0	mA	*1
			Sub Run mode	CPU/ Peripheral: 32 kHz Instruction on Flash	63	900	µA	*1, *6
			Low-speed CR Run mode	CPU/ Peripheral: 100 kHz Instruction on Flash	88	920	µA	*1
Sleep mode current	I_{CCS}		PLL Sleep mode	Peripheral: 40 MHz	9	12	mA	*1, *5
			High-speed CR Sleep mode	Peripheral: 4 MHz*2	1	2.1	mA	*1
			Sub Sleep mode	Peripheral: 32 kHz	58	880	µA	*1, *6
			Low-speed CR Sleep mode	Peripheral: 100 kHz	71	890	µA	*1

*1: When all ports are fixed.

*2: When setting it to 4 MHz by trimming.

*3: T_A=+25°C, V_{CC}=5.5 V

*4: T_A=+105°C, V_{CC}=5.5 V

*5: When using the crystal oscillator of 4 MHz(Including the current consumption of the oscillation circuit)

*6: When using the crystal oscillator of 32 kHz(Including the current consumption of the oscillation circuit)

12.3.2 Pin Characteristics

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = AVRL = 0V, T_A = - 40°C to + 105°C)

Parameter	Symbol	Pin name	Conditions	Value			Unit	Remarks
				Min	Typ	Max		
H level input voltage (hysteresis input)	V_{IHS}	CMOS hysteresis input pin, MD0, MD1	-	V_{CC} × 0.8	-	V_{CC} + 0.3	V	
		5 V tolerant input pin	-	V_{CC} × 0.8	-	V_{SS} + 5.5	V	
L level input voltage (hysteresis input)	V_{ILS}	CMOS hysteresis input pin, MD0, MD1	-	V_{SS} - 0.3	-	V_{CC} × 0.2	V	
		5 V tolerant input pin	-	V_{SS} - 0.3	-	V_{CC} × 0.2	V	
H level output voltage	V_{OH}	4mA type	V_{CC} ≥ 4.5 V, I_{OH} = - 4 mA	V_{CC} - 0.5	-	V_{CC}	V	
			V_{CC} < 4.5 V, I_{OH} = - 2 mA					
		12mA type	V_{CC} ≥ 4.5 V, I_{OH} = - 12 mA	V_{CC} - 0.5	-	V_{CC}	V	
			V_{CC} < 4.5 V, I_{OH} = - 8 mA					
L level output voltage	V_{OL}	4mA type	V_{CC} ≥ 4.5 V, I_{OL} = 4 mA	V_{SS}	-	0.4	V	
			V_{CC} < 4.5 V, I_{OL} = 2 mA					
		12mA type	V_{CC} ≥ 4.5 V, I_{OL} = 12 mA	V_{SS}	-	0.4	V	
			V_{CC} < 4.5 V, I_{OL} = 8 mA					
Input leak current	I_{IL}	-	-	- 5	-	+ 5	µA	
Pull-up resistance value	R_{PU}	Pull-up pin	V_{CC} ≥ 4.5 V	33	50	90	kΩ	
			V_{CC} < 4.5 V	-	-	180		
Input capacitance	C_{IN}	Other than VCC, VSS, AVCC, AVSS, AVRH, AVRL	-	-	5	15	pF	

CSIO (SPI = 0, SCINV = 1)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V, T_A = - 40°C to + 105°C)

Parameter	Symbol	Pin name	Conditions	V_{CC} < 4.5 V		V_{CC} ≥ 4.5 V		Unit
				Min	Max	Min	Max	
Baud rate	-	-	-	-	8	-	8	Mbps
Serial clock cycle time	t_{SCYC}	SCKx	Master mode	$4t_{CYCP}$	-	$4t_{CYCP}$	-	ns
SCK ↑ → SOT delay time	t_{SHOVI}	SCKx, SOTx		- 30	+ 30	- 20	+ 20	ns
SIN → SCK ↓ setup time	t_{IVSLI}	SCKx, SINx		50	-	30	-	ns
SCK ↓ → SIN hold time	t_{SLIXI}	SCKx, SINx		0	-	0	-	ns
Serial clock L pulse width	t_{SLSH}	SCKx	Slave mode	$2t_{CYCP}$ - 10	-	$2t_{CYCP}$ - 10	-	ns
Serial clock H pulse width	t_{SHSL}	SCKx		t_{CYCP} + 10	-	t_{CYCP} + 10	-	ns
SCK ↑ → SOT delay time	t_{SHOVE}	SCKx, SOTx		-	50	-	30	ns
SIN → SCK ↓ setup time	t_{IVSLE}	SCKx, SINx		10	-	10	-	ns
SCK ↓ → SIN hold time	t_{SLIXE}	SCKx, SINx		20	-	20	-	ns
SCK falling time	t_F	SCKx		-	5	-	5	ns
SCK rising time	t_R	SCKx		-	5	-	5	ns

Notes:

- *The above characteristics apply to clock synchronous mode.*
- *t_{CYCP} indicates the APB bus clock cycle time.*
- *About the APB bus number which Multi-function serial is connected to, see Block Diagram in this data sheet.*
- *These characteristics only guarantee the same relocate port number.*
  For example, the combination of SCKx_0 and SOTx_1 is not guaranteed.
- *When the external load capacitance C_L = 30 pF.*

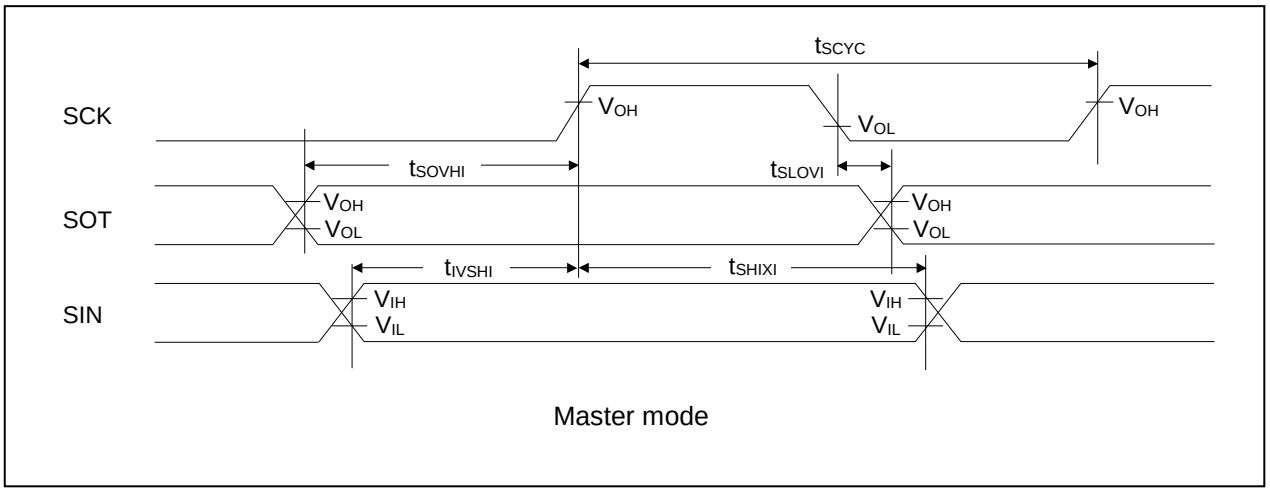
CSIO (SPI = 1, SCINV = 0)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V, T_A = - 40°C to + 105°C)

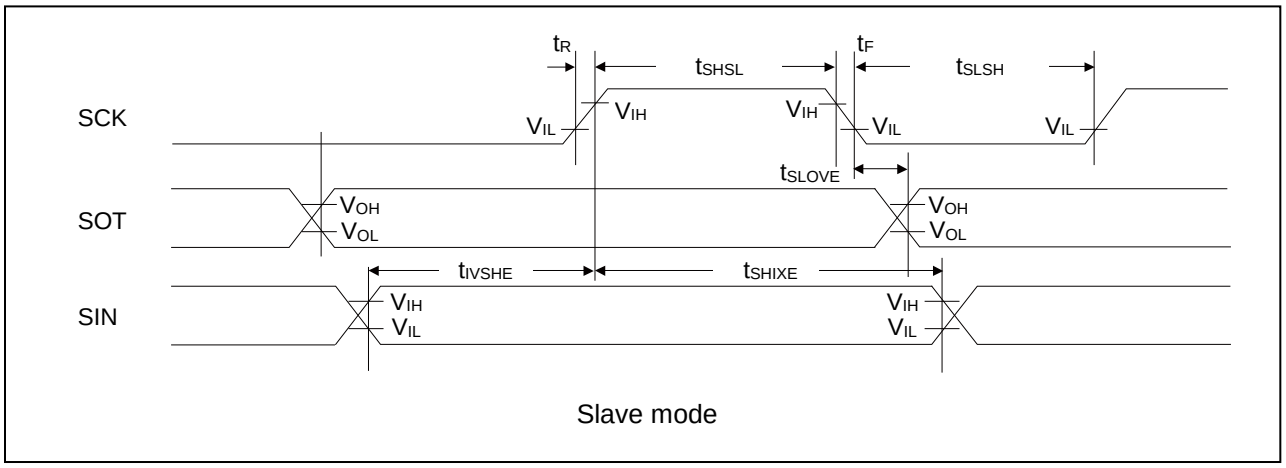
Parameter	Symbol	Pin name	Conditions	V_{CC} < 4.5 V		V_{CC} ≥ 4.5 V		Unit
				Min	Max	Min	Max	
Baud rate	-	-	-	-	8	-	8	Mbps
Serial clock cycle time	t_{SCYC}	SCKx	Master mode	$4t_{CYCP}$	-	$4t_{CYCP}$	-	ns
SCK ↑ → SOT delay time	t_{SHOVI}	SCKx, SOTx		- 30	+ 30	- 20	+ 20	ns
SIN → SCK ↓ setup time	t_{IVSLI}	SCKx, SINx		50	-	30	-	ns
SCK ↓→ SIN hold time	t_{SLIXI}	SCKx, SINx		0	-	0	-	ns
SOT → SCK ↓ delay time	t_{SOVLI}	SCKx, SOTx		$2t_{CYCP}$ - 30	-	$2t_{CYCP}$ - 30	-	ns
Serial clock L pulse width	t_{SLSH}	SCKx	Slave mode	$2t_{CYCP}$ - 10	-	$2t_{CYCP}$ - 10	-	ns
Serial clock H pulse width	t_{SHSL}	SCKx		t_{CYCP} + 10	-	t_{CYCP} + 10	-	ns
SCK ↑ → SOT delay time	t_{SHOVE}	SCKx, SOTx		-	50	-	30	ns
SIN → SCK ↓ setup time	t_{IVSLE}	SCKx, SINx		10	-	10	-	ns
SCK ↓→ SIN hold time	t_{SLIXE}	SCKx, SINx		20	-	20	-	ns
SCK falling time	t_F	SCKx		-	5	-	5	ns
SCK rising time	t_R	SCKx		-	5	-	5	ns

Notes:

- *The above characteristics apply to clock synchronous mode.*
- *t_{CYCP} indicates the APB bus clock cycle time.*
- *About the APB bus number which Multi-function serial is connected to, see Block Diagram in this data sheet.*
- *These characteristics only guarantee the same relocate port number.*
  For example, the combination of SCKx_0 and SOTx_1 is not guaranteed.
- *When the external load capacitance C_L = 30 pF.*



Master mode

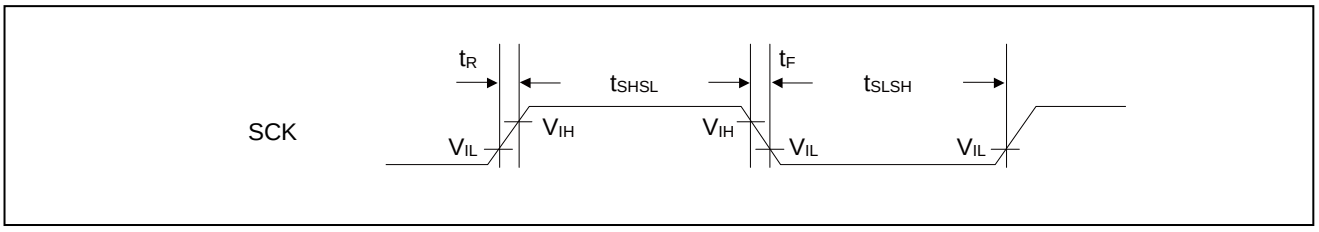


Slave mode

UART external clock input (EXT = 1)

(V_{CC} = 2.7V to 5.5V, V_{SS} = 0V, T_A = - 40°C to + 105°C)

Parameter	Symbol	Conditions	Value		Unit	Remarks
			Min	Max		
Serial clock L pulse width	t_{SLSH}	C_L = 30 pF	t_{CYCP} + 10	-	ns	
Serial clock H pulse width	t_{SHSL}		t_{CYCP} + 10	-	ns	
SCK falling time	t_F		-	5	ns	
SCK rising time	t_R		-	5	ns	



12.5 12-bit A/D Converter

Electrical characteristics for the A/D converter

(V_{CC} = AV_{CC} = 2.7V to 5.5V, V_{SS} = AV_{SS} = AVRL = 0V, T_A = - 40°C to + 105°C)

Parameter	Symbol	Pin name	Value			Unit	Remarks
			Min	Typ	Max		
Resolution	-	-	-	-	12	bit	
Integral Nonlinearity	-	-	-	± 2.0	± 4.5	LSB	AVRH = 2.7 V to 5.5 V
Differential Nonlinearity	-	-	-	± 1.5	± 2.5	LSB	
Zero transition voltage	V_{ZT}	ANxx	-	± 8	± 15	mV	
Full-scale transition voltage	V_{FST}	ANxx	-	AVRH ± 8	AVRH ± 15	mV	
Conversion time	-	-	0.8*1	-	-	µs	AV_{CC} ≥ 4.5 V
			1.0*1	-	-	µs	AV_{CC} < 4.5 V
Sampling time*2	t_S	-	0.24	-	10	µs	
Compare clock cycle*3	t_{CCK}	-	40	-	1000	ns	
State transition time to operation permission	t_{STT}	-	-	-	1.0	µs	
Analog input capacity	C_{AIN}	-	-	-	9.7	pF	
Analog input resistor	R_{AIN}	-	-	-	1.5	kΩ	AV_{CC} ≥ 4.5 V
					2.2		AV_{CC} < 4.5 V
Interchannel disparity	-	-	-	-	4	LSB	
Analog port input leak current	-	ANxx	-	-	5	µA	
Analog input voltage	-	ANxx	AVRL	-	AVRH	V	
Reference voltage	-	AVRH	2.7	-	AV_{CC}	V	
		AVRL	AV_{SS}	-	AV_{SS}		

*1: The conversion time is the value of sampling time (t_S) + compare time (t_C).

The condition of the minimum conversion time is the following.

AV_{CC} ≥ 4.5 V, HCLK=25 MHz sampling time: 240 ns, compare time: 560 ns

AV_{CC} < 4.5 V, HCLK=40 MHz sampling time: 300 ns, compare time: 700 ns

Ensure that it satisfies the value of the sampling time (t_S) and compare clock cycle (t_{CCK}).

For setting of the sampling time and compare clock cycle, see Chapter 1-1: A/D Converter in FM3 Family Peripheral Manual Analog Macro Part.

The register settings of the A/D Converter are reflected in the operation according to the APB bus clock timing.

For the number of the APB bus to which the A/D Converter is connected, see Block Diagram.

The Base clock (HCLK) is used to generate the sampling time and the compare clock cycle.

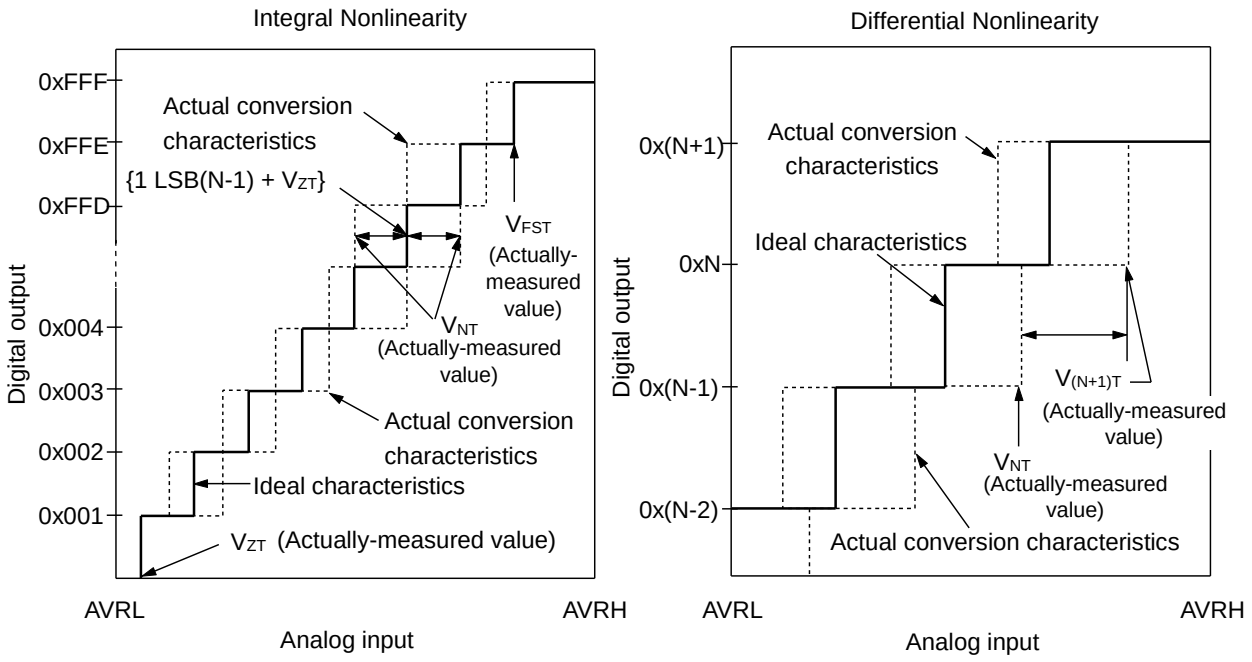
*2: A necessary sampling time changes by external impedance.

Ensure that it sets the sampling time to satisfy (Equation 1).

*3: The compare time (t_C) is the value of (Equation 2).

Definition of 12-bit A/D Converter Terms

- Resolution: Analog variation that is recognized by an A/D converter.
- Integral Nonlinearity: Deviation of the line between the zero-transition point (0b000000000000 ⟷ 0b000000000001) and the full-scale transition point (0b111111111110 ⟷ 0b111111111111) from the actual conversion characteristics.
- Differential Nonlinearity: Deviation from the ideal value of the input voltage that is required to change the output code by 1 LSB.



$$\text{Integral Nonlinearity of digital output N} = \frac{V_{NT} - \{1LSB \times (N - 1) + V_{ZT}\}}{1LSB} \text{ [LSB]}$$

$$\text{Differential Nonlinearity of digital output N} = \frac{V_{(N+1)T} - V_{NT}}{1LSB} - 1 \text{ [LSB]}$$

$$1LSB = \frac{V_{FST} - V_{ZT}}{4094}$$

N: A/D converter digital output value.
V_{ZT}: Voltage at which the digital output changes from 0x000 to 0x001.
V_{FST}: Voltage at which the digital output changes from 0xFFE to 0xFFF.
V_{NT}: Voltage at which the digital output changes from 0x(N − 1) to 0xN.

12.7.2 Interrupt of Low-Voltage Detection

(T_A = - 40°C to + 105°C)

Parameter	Symbol	Conditions	Value			Unit	Remarks
			Min	Typ	Max		
Detected voltage	VDL	SVHI = 00011	2.58	2.80	3.02	V	When voltage drops
Released voltage	VDH		2.67	2.90	3.13	V	When voltage rises
Detected voltage	VDL	SVHI = 00100	2.76	3.00	3.24	V	When voltage drops
Released voltage	VDH		2.85	3.10	3.35	V	When voltage rises
Detected voltage	VDL	SVHI = 00101	2.94	3.20	3.46	V	When voltage drops
Released voltage	VDH		3.04	3.30	3.56	V	When voltage rises
Detected voltage	VDL	SVHI = 00110	3.31	3.60	3.89	V	When voltage drops
Released voltage	VDH		3.40	3.70	4.00	V	When voltage rises
Detected voltage	VDL	SVHI = 00111	3.40	3.70	4.00	V	When voltage drops
Released voltage	VDH		3.50	3.80	4.10	V	When voltage rises
Detected voltage	VDL	SVHI = 01000	3.68	4.00	4.32	V	When voltage drops
Released voltage	VDH		3.77	4.10	4.43	V	When voltage rises
Detected voltage	VDL	SVHI = 01001	3.77	4.10	4.43	V	When voltage drops
Released voltage	VDH		3.86	4.20	4.54	V	When voltage rises
Detected voltage	VDL	SVHI = 01010	3.86	4.20	4.54	V	When voltage drops
Released voltage	VDH		3.96	4.30	4.64	V	When voltage rises
LVD stabilization wait time	t_{LVDW}	-	-	-	8160 × t_{CYCP}*	µs	
LVD detection delay time	t_{LVDDL}	-	-	-	200	µs	

*: t_{CYCP} indicates the APB2 bus clock cycle time.

12.8 Flash Memory Write/Erase Characteristics

12.8.1 Write / Erase time

(V_{CC} = 2.7V to 5.5V, T_A = - 40°C to + 105°C)

Parameter	Value		Unit	Remarks
	Typ	Max		
Sector erase time	0.3	0.7	s	Includes write time prior to internal erase
Half word (16-bit) write time	16	282	µs	Not including system-level overhead time
Chip erase time	2.4	5.6	s	Includes write time prior to internal erase

*: The typical value is immediately after shipment, the maximum value is guarantee value under 10,000 cycle of erase/write.

12.8.2 Write cycles and data hold time

Erase/write cycles (cycle)	Data hold time (year)	Remarks
1,000	20*	
10,000	10*	

*: At average + 85°C